

제23회 한국반도체학술대회

2016년 2월 22일(월)-24일(수), 강원도 하이원리조트

K. Memory (Design & Process Technology) 분과

Room J

청옥 I (6층)

2016년 2월 23일(화) 08:30-10:30

[TJ1-K] Memory Processing and RRAM Operation

좌장 : 김수길(SK 하이닉스), 백승재(한경대학교)

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| TJ1-K-1 | 08:30-08:45 | Reliability of Hour-Glass Shaped Filament in a Cu-based Al₂O₃/WO₃ Conductive Bridge RAM System
Jiyong Woo and Hyunsang Hwang
<i>Department of Materials Science and Engineering, Pohang University of Science and Technology</i> |
| TJ1-K-2 | 08:45-09:15 | [초청] ALD Technologies and Applications in Memory Device Fabrication
Han-Jin Lim, Seok-Woo Nam, Siyoung Choi, and Ho-Kyu Kang
<i>Semiconductor R&D Center, Samsung Electronics Co. Ltd.</i> |
| TJ1-K-3 | 09:15-09:30 | Suppression of the Reset Breakdown Failure by using RuO₂ Electrode in HfOx-based RRAM
Jaesung Park, Jiyong Woo, Amit Prakash, Kibong Moon, Changhyuck Sung, and Hyunsang Hwang
<i>Department of Materials and Science Engineering, Pohang University of Science and Technology</i> |
| TJ1-K-4 | 09:30-09:45 | Effects of N-GST Buffer Layer on Switching Characteristics of CBRAM
Seokjae Lim, Sangheon Lee, Jiyong Woo, and Hyungsang Hwang
<i>Department of Materials and Science Engineering, Pohang University of Science and Technology</i> |
| TJ1-K-5 | 09:45-10:00 | Exploring Non-polar and Bipolar Resistance Switching Mechanisms from TiN/TiO₂/Al Memory
Xing Long Shao ¹ , Kyung Min Kim ² , Kyung Jean Yoon ¹ , Seul Ji Song ¹ , Jung Ho Yoon ¹ , Tae Hyung Park ¹ , Dae Eun Kwon ¹ , Young Jae Kwon ¹ , Hye Jin Kim ¹ , and Cheol Seong Hwang ¹
¹ Korea ¹ Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University, ² Hewlett-Packard Laboratories, Hewlett-Packard Company Palo Alto, USA |
| TJ1-K-6 | 10:00-10:15 | Enhancement of Switching and Endurance Characteristics of ReRAM by Control of Forming Conditions
이재연, 하태정, 박우영, 김경완, 박용택, 배윤철, 김종일, 김수길
<i>NM 공정개발그룹, R&D 부문, SK hynix Inc.</i> |
| TJ1-K-7 | 10:15-10:30 | Effects of Gate Bias on Reset Failure in HfO₂ based 1T1R ReRAM Cell |

The 23rd Korean Conference on Semiconductors (KCS 2016)

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Changhyuck Sung, Jeonghwan Song, Sangheon Lee, and Hyunsang Hwang
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